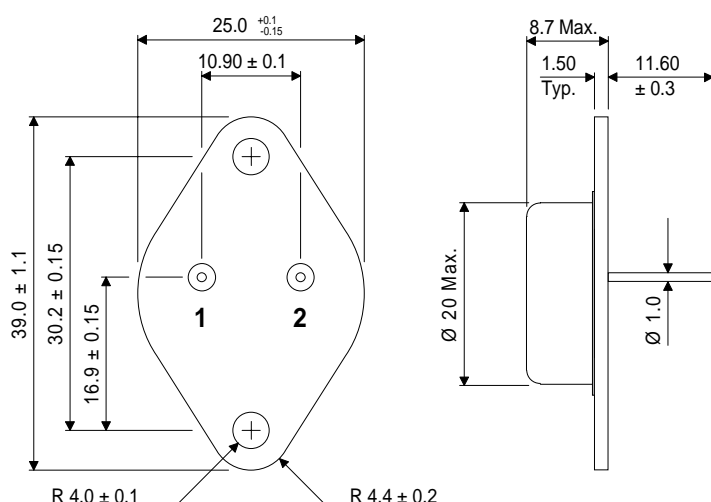


## MECHANICAL DATA

Dimensions in mm

## N-CHANNEL POWER MOSFET

### POWER MOSFETS FOR AUDIO APPLICATIONS



### TO-3

Pin 1 – Gate

Pin 2 – Drain

Case – Source

### FEATURES

- HIGH SPEED SWITCHING
- N-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- P-CHANNEL ALSO AVAILABLE AS BUZ905D & BUZ906D
- DOUBLE DIE PACKAGE FOR MAXIMUM POWER AND HEATSINK SPACE

## ABSOLUTE MAXIMUM RATINGS

( $T_{case} = 25^{\circ}C$  unless otherwise stated)

		<b>BUZ900D</b>	<b>BUZ901D</b>
$V_{DSX}$	Drain – Source Voltage	160V	200V
$V_{GSS}$	Gate – Source Voltage	$\pm 14V$	
$I_D$	Continuous Drain Current	16A	
$I_{D(PK)}$	Body Drain Diode	16A	
$P_D$	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	250W	
$T_{stg}$	Storage Temperature Range	$-55$ to $150^{\circ}C$	
$T_j$	Maximum Operating Junction Temperature	$150^{\circ}C$	
$R_{\theta JC}$	Thermal Resistance Junction – Case	$0.5^{\circ}C/W$	

## STATIC CHARACTERISTICS ( $T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$BV_{\text{DSX}}$ Drain – Source Breakdown Voltage	$V_{\text{GS}} = -10\text{V}$	160			V
	$I_{\text{D}} = 10\text{mA}$	200			
$BV_{\text{GSS}}$ Gate – Source Breakdown Voltage	$V_{\text{DS}} = 0$ $I_{\text{G}} = \pm 100\mu\text{A}$	$\pm 14$			V
$V_{\text{GS(OFF)}}$ Gate – Source Cut-Off Voltage	$V_{\text{DS}} = 10\text{V}$ $I_{\text{D}} = 100\text{mA}$	0.1		1.5	V
$V_{\text{DS(SAT)}}^*$ Drain – Source Saturation Voltage	$V_{\text{GD}} = 0$ $I_{\text{D}} = 16\text{A}$			12	V
$I_{\text{DSX}}$ Drain – Source Cut-Off Current	$V_{\text{GS}} = -10\text{V}$	$V_{\text{DS}} = 160\text{V}$ BUZ900D		10	mA
		$V_{\text{DS}} = 200\text{V}$ BUZ901D		10	
$y_{\text{fs}}^*$ Forward Transfer Admittance	$V_{\text{DS}} = 10\text{V}$ $I_{\text{D}} = 3\text{A}$	1.4		4	S

## DYNAMIC CHARACTERISTICS ( $T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$C_{\text{iss}}$ Input Capacitance	$V_{\text{DS}} = 10\text{V}$ $f = 1\text{MHz}$		950		pF
$C_{\text{oss}}$ Output Capacitance			550		
$C_{\text{rss}}$ Reverse Transfer Capacitance			18		
$t_{\text{on}}$ Turn-on Time	$V_{\text{DS}} = 20\text{V}$ $I_{\text{D}} = 7\text{A}$		160		ns
$t_{\text{off}}$ Turn-off Time			80		

\* Pulse Test: Pulse Width =  $300\mu\text{s}$  , Duty Cycle  $\leq 2\%$ .

